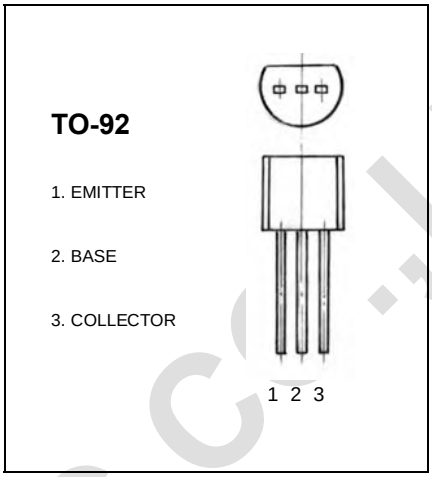
MPSA55 TRANSISTOR (PNP)



FEATURES

Power dissipation

$P_{CM:}$ 0.625 W (Tamb=25℃)

Collector current

I_{CM}: -0.5 A

Collector-base voltage

$V_{(BR)CBO}$: -60 V

Operating and storage junction temperature range

T_J, T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-BASE breakdown voltage	$V_{(BR)CBO}$	Ic=-0.1mA, I_B=0	-60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	Ic=-1 mA, I_B=0	-60			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-0.1mA, I_C=0	-4			V
Collector cut-off current	I_{CBO}	V_{CB}=-60 V, I_E=0			-0.1	μA
Collector cut-off current	I_{CEO}	V_{CE}=-60V, I_C=0			-0.1	μA
DC current gain	h_{FE}	V_{CE}=-1V, I_C=-100mA	100			
Collector-emitter saturation voltage	V_{CE}(sat)	I_C=-100 mA, I_B=-10mA			-0.25	V
Base-Emitter Saturation Voltage	V_{BE}	V_{CE}=-1V, I_C=-100mA			-1.2	V
Transition frequency	f_T	V_{CE}=-1V, I_C=-100mA f=100MHz	50			MHz